

1/4

FIG 1

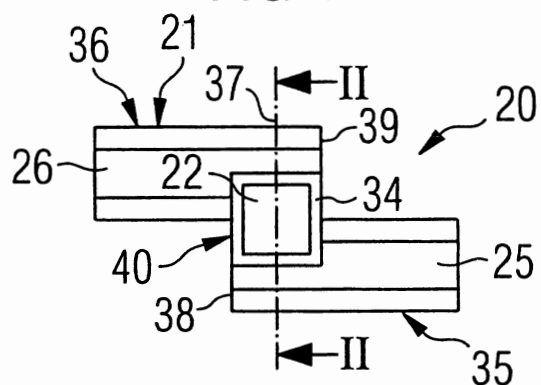


FIG 2

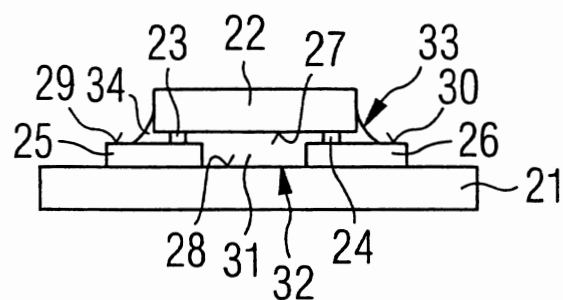


FIG 3



FIG 4

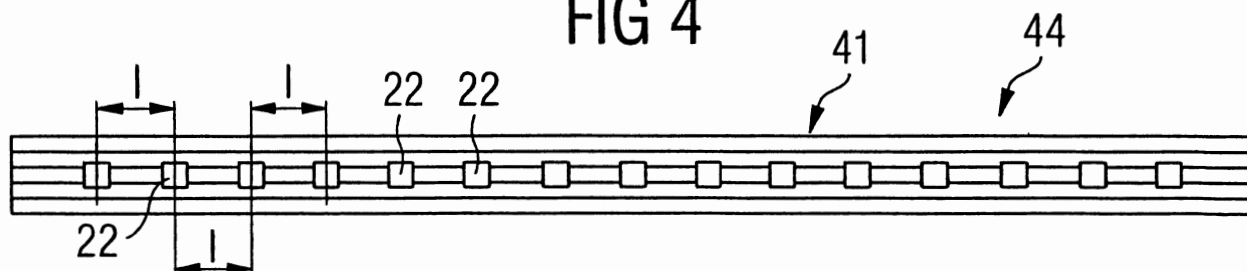


FIG 5

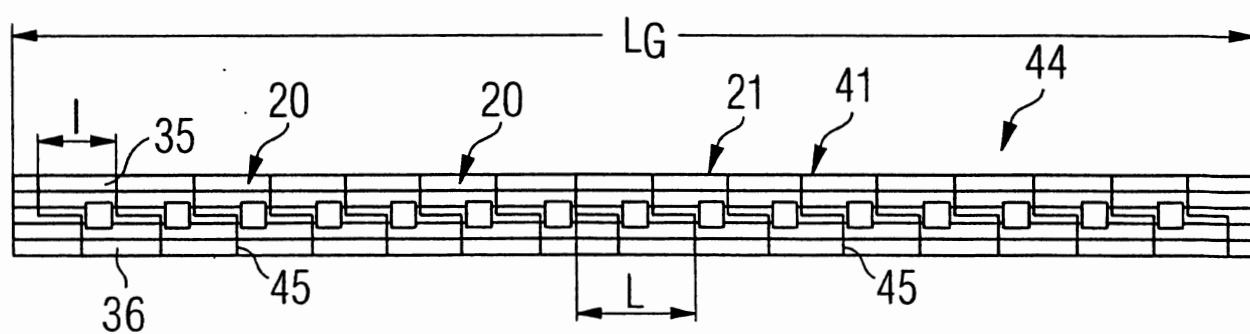


FIG 6

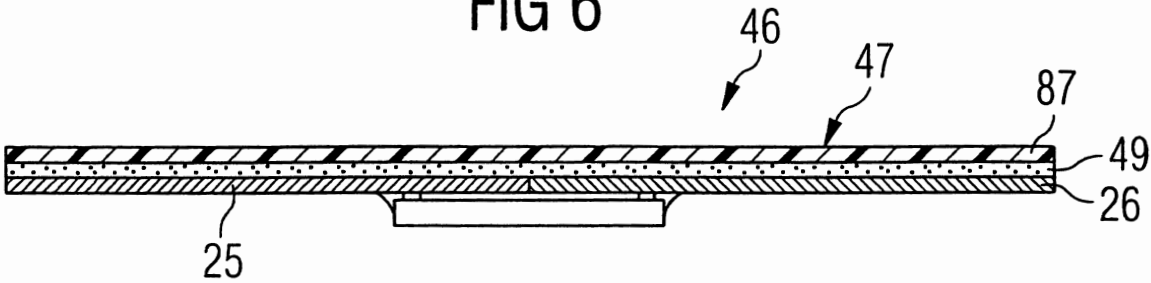
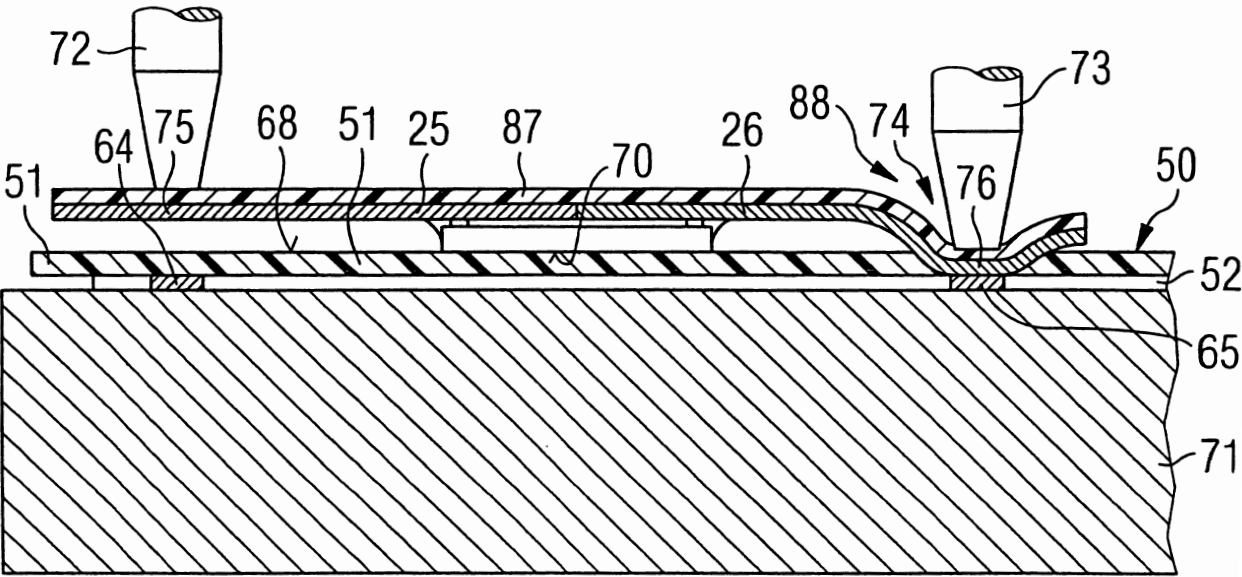


FIG 7





[illegible]

Figure 1 is a cross-sectional view of a semiconductor device 20. The device is mounted on a base 64. It consists of a substrate 50, a thin layer 26, a patterned layer 51, and a top layer 87. A probe 75 is shown on the left and a probe 89 is shown on the right. The device is mounted on a base 64.